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March 2015

## FGH60N60SF 600 V, 60 A Field Stop IGBT

#### **Features**

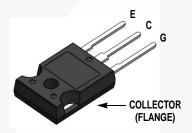
- · High Current Capability
- Low Saturation Voltage: V<sub>CE(sat)</sub> = 2.3 V @ I<sub>C</sub> = 60 A
- High Input Impedance
- Fast Switching
- RoHS Compliant

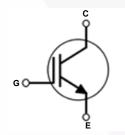
#### **Applications**

• Solar Inverter, UPS, Welder, PFC

## **General Description**

Using novel field stop IGBT technology, Fairchild's field stop IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.





## **Absolute Maximum Ratings**

Symbol	Description  Collector to Emitter Voltage		Ratings	Unit V	
V <sub>CES</sub>			600		
V <sub>GES</sub>	Gate to Emitter Voltage Transient Gate-to-Emitter Voltage		±20	V	
			±30	V	
I <sub>C</sub>	Collector Current	$^{\circ}$ T <sub>C</sub> = 25 $^{\circ}$ C	120	А	
	Collector Current	$@ T_C = 100^{\circ}C$	60	А	
I <sub>CM (1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	180	A	
P <sub>D</sub>	Maximum Power Dissipation	$@ T_C = 25^{\circ}C$	378	W	
	Maximum Power Dissipation	$@ T_C = 100^{\circ}C$	151	W	
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C	
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

1: Repetitive test, Pulse width limited by max. juntion temperature

#### **Thermal Characteristics**

Symbol	pol Parameter		Max.	Unit
$R_{\theta JC}(IGBT)$	GBT) Thermal Resistance, Junction to Case		0.33	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

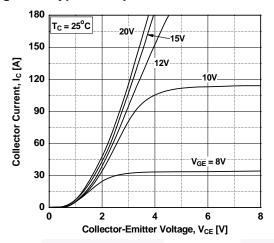
## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH60N60SFTL	FGH60N60SF	TO-247	Tube	N/A	N/A	30

## Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \mu\text{A}$	600	-	-	V
$\Delta BV_{CES}$ / $\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0 \text{ V, } I_{C} = 250 \mu\text{A}$	-	0.4	-	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0 V	-	-	250	μΑ
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA
On Charac	teristics			1		
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_{C} = 250 \mu\text{A},  V_{CE} = V_{GE}$	4.0	5.0	6.5	V
GE(III)		I <sub>C</sub> = 60 A, V <sub>GE</sub> = 15 V	_	2.3	2.9	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 60 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 125°C	-	2.5	-	V
Dynamic C	haracteristics	,				
C <sub>ies</sub>	Input Capacitance		-	2820	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1  MHz	-	350	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	- 1 = 1 IVII IZ	-	140	-	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time		-	22	-	ns
t <sub>r</sub>	Rise Time		-	42	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 60 \text{ A},$	-	134	-	ns
t <sub>f</sub>	Fall Time	$R_G = 5 \Omega$ , $V_{GE} = 15 V$ ,	-	31	62	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C	-	1.79	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		- /	0.67	-	mJ
E <sub>ts</sub>	Total Switching Loss		-/	2.46	-	mJ
t <sub>d(on)</sub>	Turn-On Delay Time		_	22	- /	ns
t <sub>r</sub>	Rise Time		-	44	- 1/	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC}$ = 400 V, $I_{C}$ = 60 A, $R_{G}$ = 5 $\Omega$ , $V_{GE}$ = 15 V, Inductive Load, $T_{C}$ = 125°C	-	144	<u>-</u>	ns
t <sub>f</sub>	Fall Time		-	43	/ -	ns
E <sub>on</sub>	Turn-On Switching Loss		-	1.88	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	1.0	- [	mJ
E <sub>ts</sub>	Total Switching Loss		-	2.88	-	mJ
Qg	Total Gate Charge		-	198	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	$V_{CE} = 400 \text{ V}, I_{C} = 60 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	22	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	▼GE - 13 ▼	-	106	-	nC

Figure 1. Typical Output Characteristics



**Figure 2. Typical Output Characteristics** 

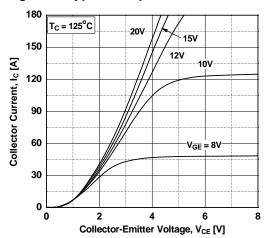


Figure 3. Typical Saturation Voltage Characteristics

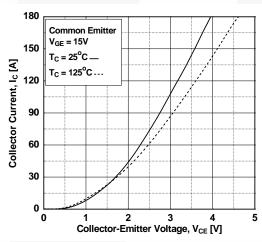


Figure 4. Transfer Characteristics

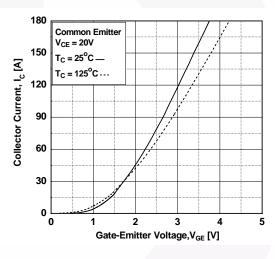


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

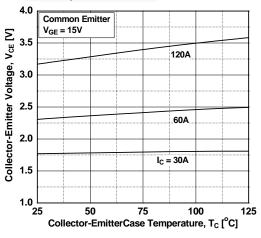


Figure 6. Saturation Voltage vs.  $V_{GE}$ 

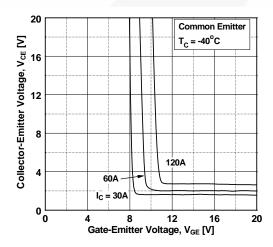


Figure 7. Saturation Voltage vs. V<sub>GE</sub>

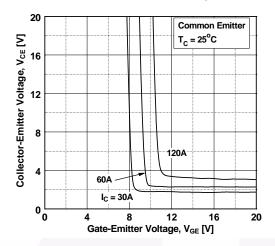


Figure 9. Capacitance Characteristics

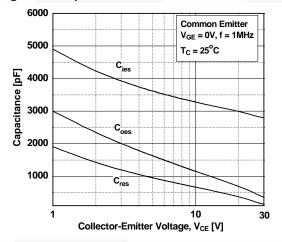


Figure 11. SOA Characteristics

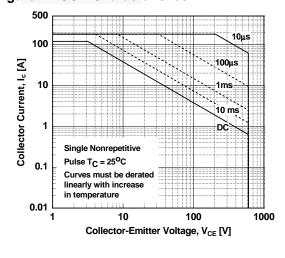


Figure 8. Saturation Voltage vs. V<sub>GE</sub>

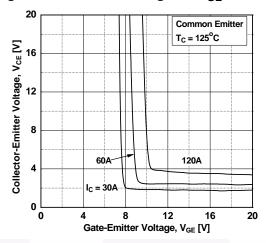


Figure 10. Gate charge Characteristics

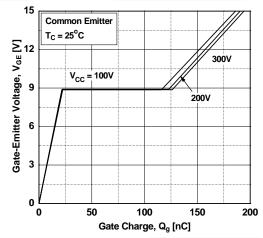


Figure 12. Turn off Switching SOA Characteristics

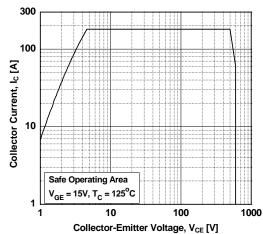


Figure 13. Turn-on Characteristics vs.
Gate Resistance

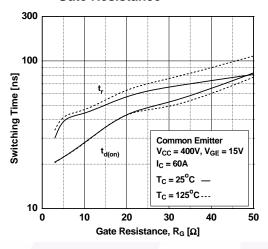


Figure 14. Turn-off Characteristics vs.
Gate Resistance

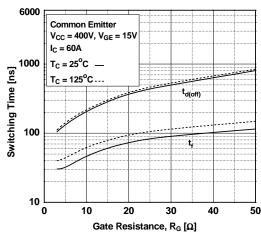


Figure 15. Turn-on Characteristics vs. Collector Current

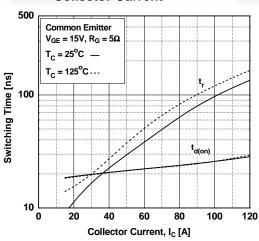


Figure 16. Turn-off Characteristics vs. Collector Current

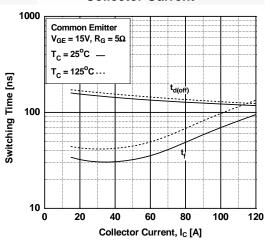


Figure 17. Switching Loss vs Gate Resistance

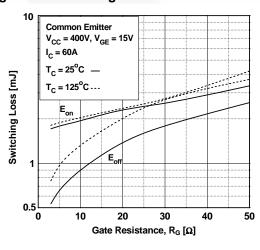


Figure 18. Switching Loss vs Collector Current

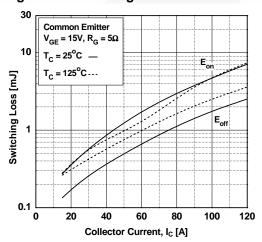
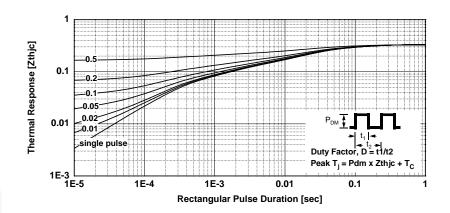
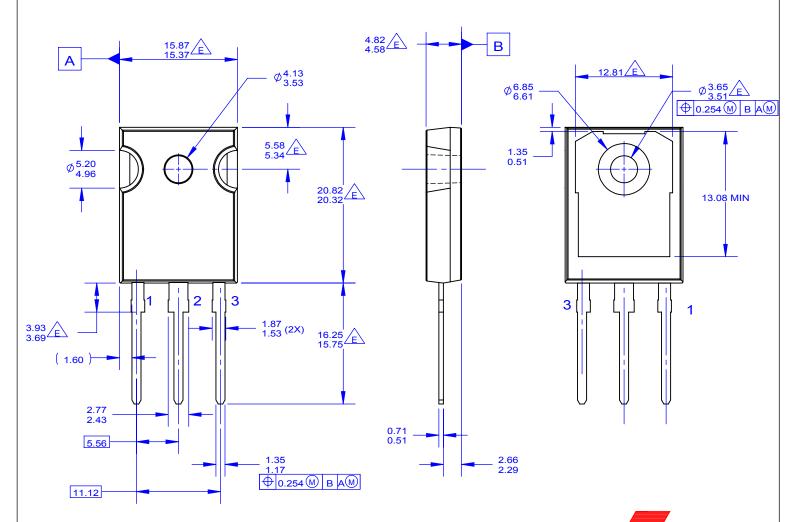


Figure 19. Transient Thermal Impedance of IGBT







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